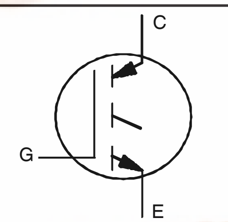
PD - 94545C

International
IOR Rectifier

IRGB8B60K
IRGS8B60K
IRGSL8B60K

INSULATED GATE BIPOLAR TRANSISTOR

Features
- Low VCE (on) Non Punch Through IGBT Technology.
- 10μs Short Circuit Capability.
- Square RBSOA.
- Positive VCE (on) Temperature Coefficient.



n-channel

V_{CES} = 600V

I_C = 20A, T_C=100°C

t_{sc}>10μs, T_J=150°C

$V_{CE(on)}$ typ. = 1.8V

Benefits
- Benchmark Efficiency for Motor Control.
- Rugged Transient Performance.
- Low EMI.
- Excellent Current Sharing in Parallel Operation.

TO-220AB IRGB8B60K | D2Pak IRGS8B60K | TO-262 IRGSL8B60K

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
I_C @ T_C = 25°C	Continuous Collector Current	28	A
I_C @ T_C = 100°C	Continuous Collector Current	19	
I_{CM}	Pulse Collector Current (Ref.Fig.C.T.5)	56	
I_{LM}	Clamped Inductive Load current ①	56	
V_{GE}	Gate-to-Emitter Voltage	±20	V
P_D @ T_C = 25°C	Maximum Power Dissipation	167	W
P_D @ T_C = 100°C	Maximum Power Dissipation	83	
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +175	°C
	Storage Temperature Range, for 10 sec.	300 (0.063 in. (1.6mm) from case)	

Thermal / Mechanical Characteristics

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case- IGBT	——	——	0.90	°C/W
$R_{\theta CS}$	Case-to-Sink, flat, greased surface	——	0.50	——	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount ②	——	——	62	
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount, Steady State)③	——	——	40	
	Weight	——	1.44	——	g

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig.
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V_{GE} = 0V, I_C = 500µA	
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	—	0.57	—	V/°C	V_{GE} = 0V, I_C = 1mA (25°C-150°C)	
$V_{CE(on)}$	Collector-to-Emitter Voltage	—	1.8	2.2	V	I_C = 8.0A, V_{GE} = 15V, T_J = 25°C	5,6,7
		—	2.2	2.5		I_C = 8.0A, V_{GE} = 15V, T_J = 150°C	8,9,10
		—	2.3	2.6		I_C = 8.0A, V_{GE} = 15V, T_J = 175°C	
$V_{GE(th)}$	Gate Threshold Voltage	3.5	4.5	5.5		V_{CE} = V_{GE}, I_C = 250µA	8,9,10,
$\Delta V_{GE(th)}/\Delta T_J$	Threshold Voltage temp. coefficient	—	-9.5	—	mV/°C	V_{CE} = V_{GE}, I_C = 1mA (25°C-125°C)	11
gfe	Forward Transconductance	—	3.7	—	S	V_{CE} = 50V, I_C = 8.0A, PW = 80µs	
I_{CES}	Zero Gate Voltage Collector Current	—	1.0	150	µA	V_{GE} = 0V, V_{CE} = 600V	
		—	200	500		V_{GE} = 0V, V_{CE} = 600V, T_J = 150°C	
		—	800	1320		V_{GE} = 0V, V_{CE} = 600V, T_J = 175°C	
I_{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V_{GE} = ±20V	

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions	Ref.Fig.
Q_g	Total Gate Charge (turn-on)	—	29	—	nC	I_C = 8.0A	17
Q_{ge}	Gate-to-Emitter Charge (turn-on)	—	3.7	—		V_{CC} = 480V	CT1
Q_{gc}	Gate-to-Collector Charge (turn-on)	—	14	—		V_{GE} = 15V	
E_{on}	Turn-On Switching Loss	—	160	268	µJ	I_C = 8.0A, V_{CC} = 400V	CT4
E_{off}	Turn-Off Switching Loss	—	160	268		V_{GE} = 15V, R_G = 50Ω, L = 1.1mH	
E_{tot}	Total Switching Loss	—	320	433		T_J = 25°C ④	
$t_{d(on)}$	Turn-On delay time	—	23	27	ns	I_C = 8.0A, V_{CC} = 400V	
t_r	Rise time	—	22	26		V_{GE} = 15V, R_G = 50Ω, L = 1.1mH	CT4
$t_{d(off)}$	Turn-Off delay time	—	140	150		T_J = 25°C	
t_f	Fall time	—	32	42			
E_{on}	Turn-On Switching Loss	—	220	330	µJ	I_C = 8.0A, V_{CC} = 400V	CT4
E_{off}	Turn-Off Switching Loss	—	270	381		V_{GE} = 15V, R_G = 50Ω, L = 1.1mH	12,14
E_{tot}	Total Switching Loss	—	490	608		T_J = 150°C ④	WF1,WF2
$t_{d(on)}$	Turn-On delay time	—	22	27	ns	I_C = 8.0A, V_{CC} = 400V	13,15
t_r	Rise time	—	21	25		V_{GE} = 15V, R_G = 50Ω, L = 1.1mH	CT4
$t_{d(off)}$	Turn-Off delay time	—	180	198		T_J = 150°C	WF1
t_f	Fall time	—	40	56			WF2
C_{ies}	Input Capacitance	—	440	—	pF	V_{GE} = 0V	
C_{oes}	Output Capacitance	—	38	—		V_{CC} = 30V	16
C_{res}	Reverse Transfer Capacitance	—	16	—		f = 1.0MHz	
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				T_J = 150°C, I_C = 34A, Vp = 600V V_{CC}=500V,V_{GE} = +15V to 0V,R_G = 50Ω	4 CT2
SCSOA	Short Circuit Safe Operating Area	10	—	—	µs	T_J = 150°C, Vp = 600V, R_G = 100Ω V_{CC}=360V,V_{GE} = +15V to 0V	CT3 WF3

Notes ① to ④ are on page 13.

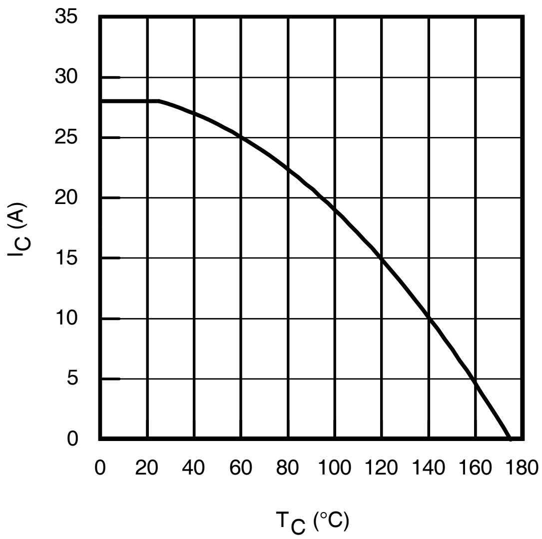


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

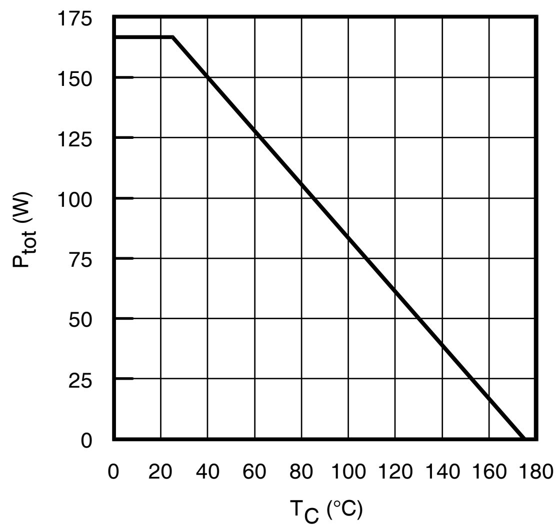


Fig. 2 - Power Dissipation vs. Case Temperature

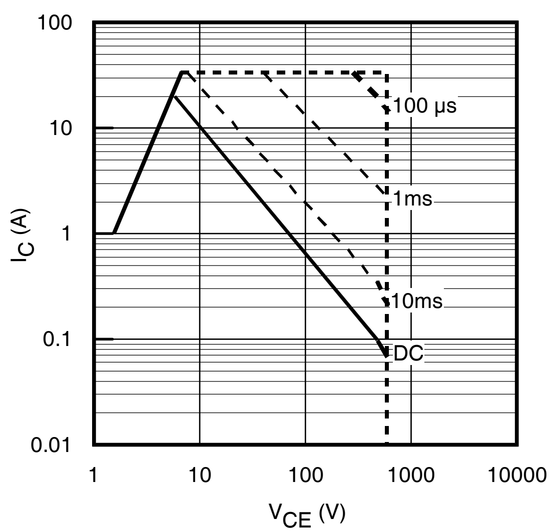


Fig. 3 - Forward SOA
T_C = 25°C; $T_J \leq$ 150°C

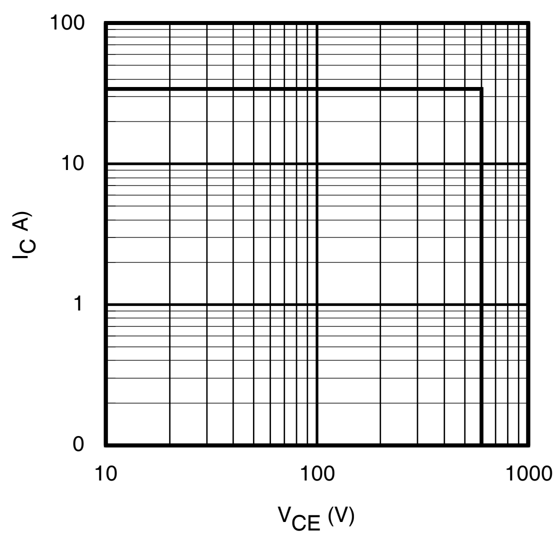


Fig. 4 - Reverse Bias SOA
T_J = 150°C; V_{GE} =15V

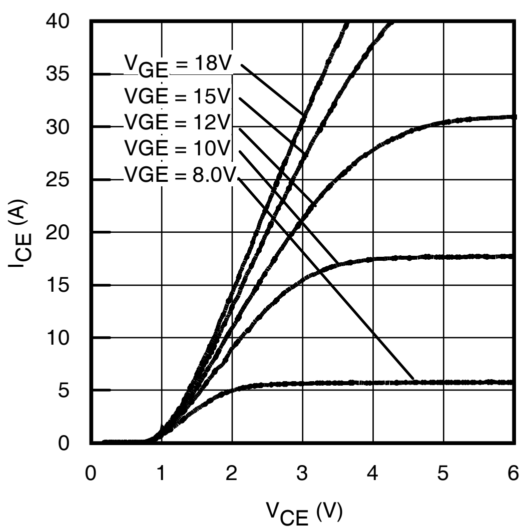


Fig. 5 - Typ. IGBT Output Characteristics
T_J = -40°C; tp = 80µs

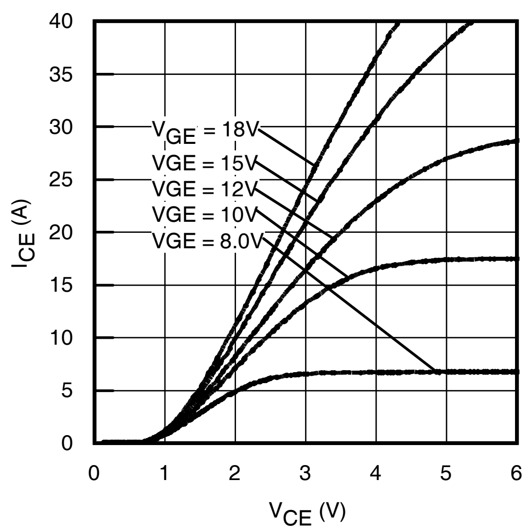


Fig. 6 - Typ. IGBT Output Characteristics
T_J = 25°C; tp = 80µs

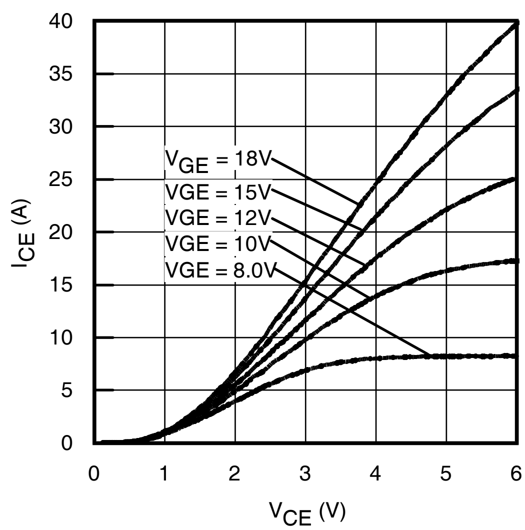


Fig. 7 - Typ. IGBT Output Characteristics
T_J = 150°C; tp = 80µs

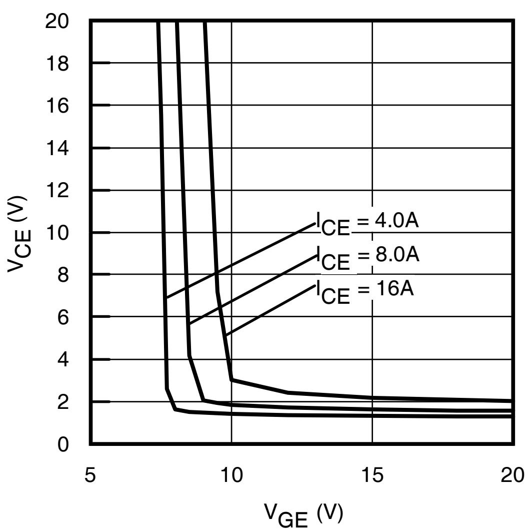


Fig. 8 - Typical V_{CE} vs. V_{GE}
T_J = -40°C

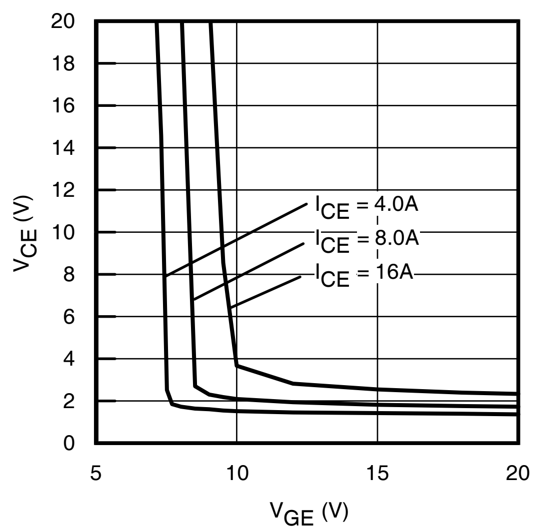


Fig. 9 - Typical V_{CE} vs. V_{GE}
T_J = 25°C

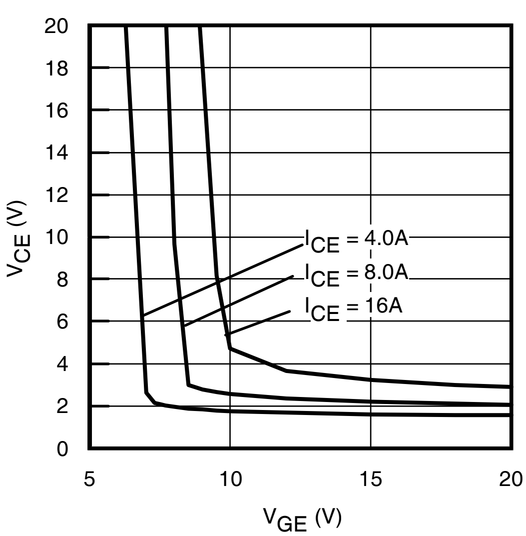


Fig. 10 - Typical V_{CE} vs. V_{GE}
T_J = 150°C

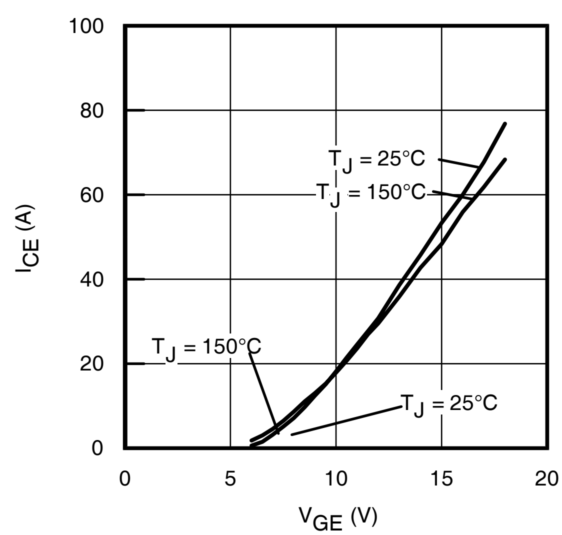


Fig. 11 - Typ. Transfer Characteristics
V_{CE} = 360V; tp = 10µs

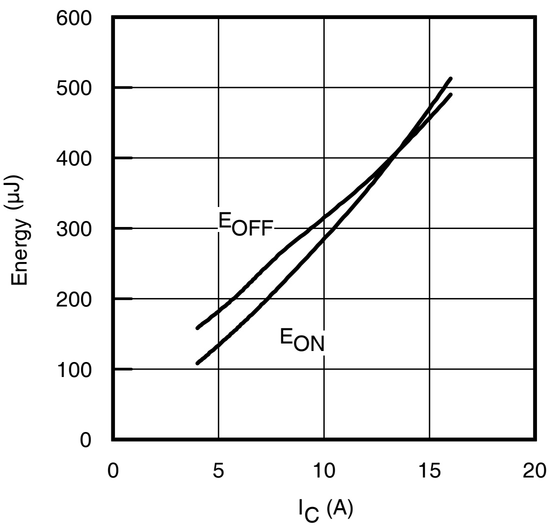


Fig. 12 - Typ. Energy Loss vs. I_C
T_J = 150°C; L=1.1mH; V_{CE}= 400V,
R_G= 50Ω; V_{GE}= 15V

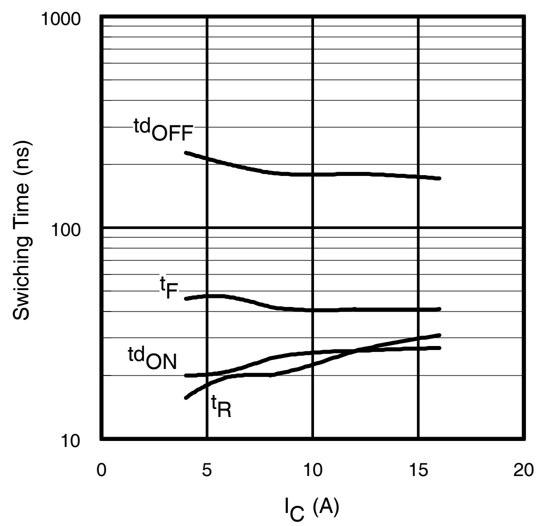


Fig. 13 - Typ. Switching Time vs. I_C
T_J = 150°C; L=1.1mH; V_{CE}= 400V
R_G= 50Ω; V_{GE}= 15V

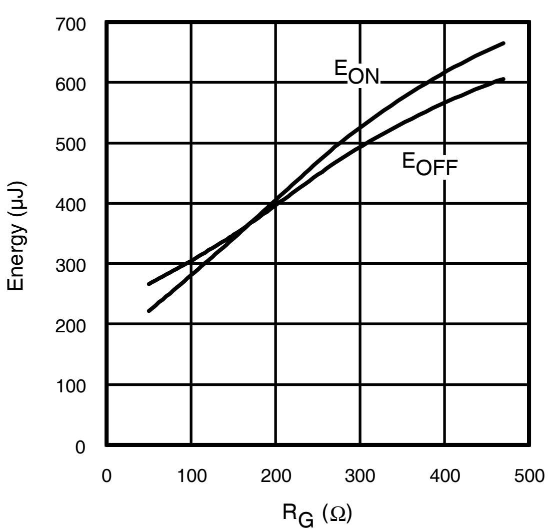


Fig. 14 - Typ. Energy Loss vs. R_G
T_J = 150°C; L=1.1mH; V_{CE}= 400V
I_{CE}= 8.0A; V_{GE}= 15V

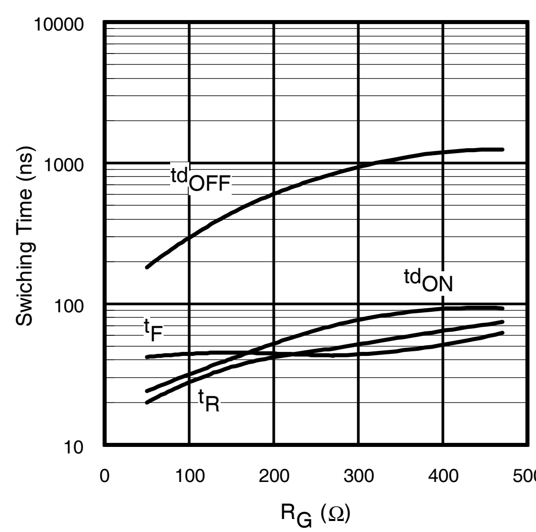


Fig. 15 - Typ. Switching Time vs. R_G
T_J = 150°C; L=1.1mH; V_{CE}= 400V
I_{CE}= 8.0A; V_{GE}= 15V

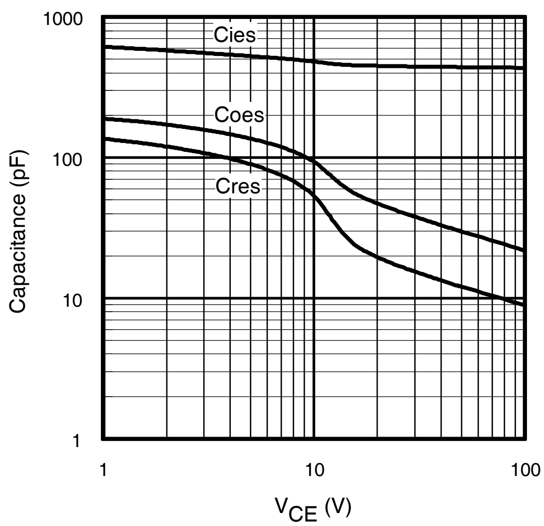


Fig. 16- Typ. Capacitance vs. V_{CE}
V_{GE}= 0V; f = 1MHz

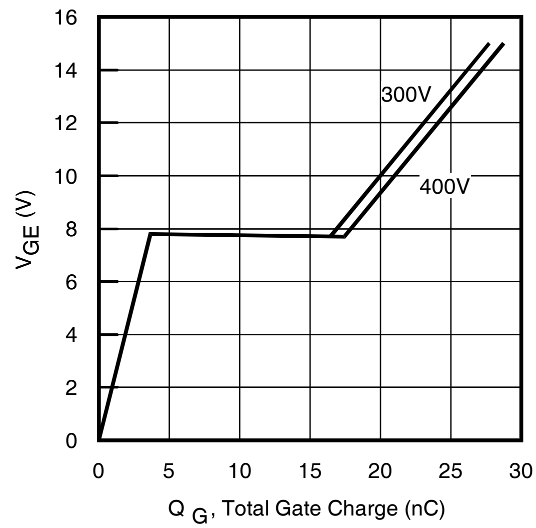


Fig. 17 - Typical Gate Charge vs. V_{GE}
I_{CE} = 8.0A; L = 600µH

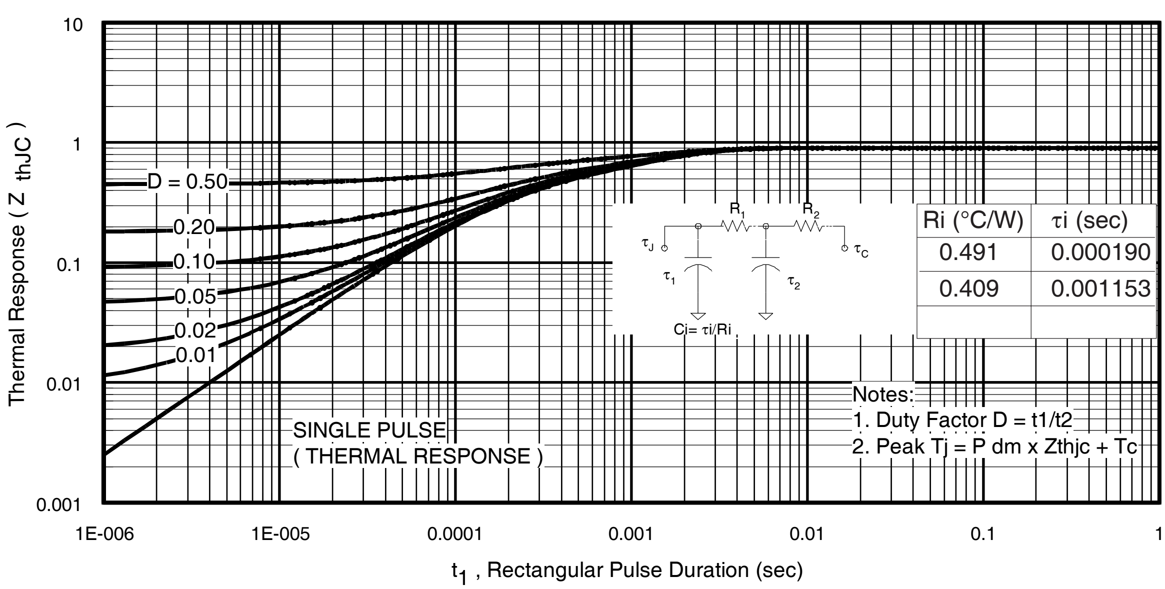


Fig 18. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

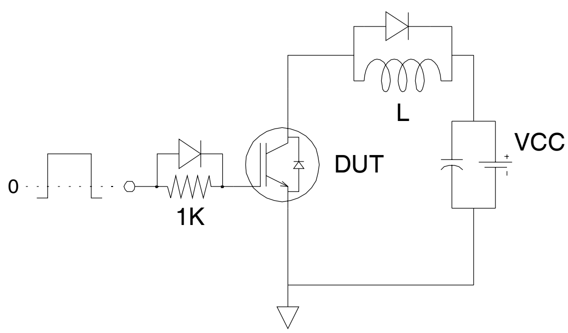


Fig.C.T.1 - Gate Charge Circuit (turn-off)

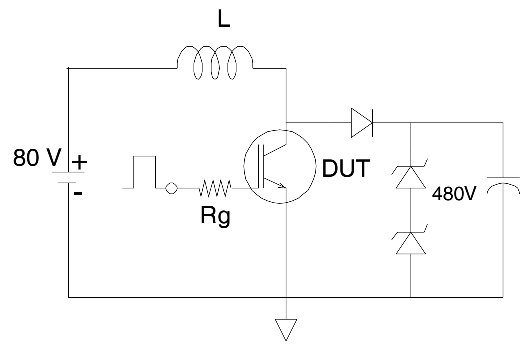


Fig.C.T.2 - RBSOA Circuit

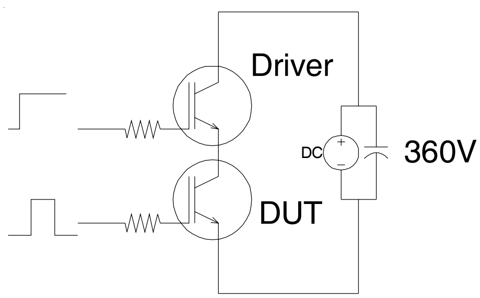


Fig.C.T.3 - S.C.SOA Circuit

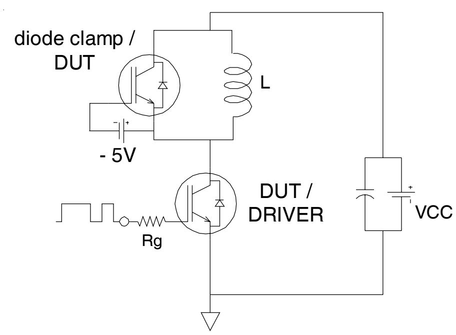


Fig.C.T.4 - Switching Loss Circuit

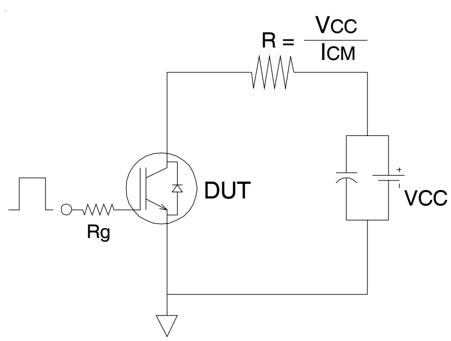


Fig.C.T.5 - Resistive Load Circuit

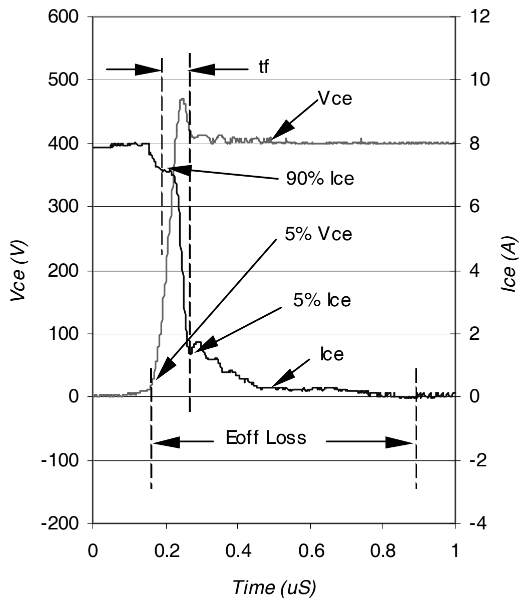


Fig. WF1- Typ. Turn-off Loss Waveform
@ T_J = 150°C using Fig. CT.4

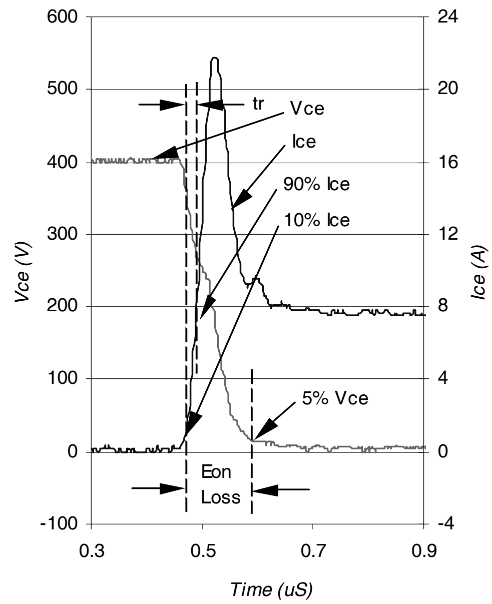


Fig. WF2- Typ. Turn-on Loss Waveform
@ T_J = 150°C using Fig. CT.4

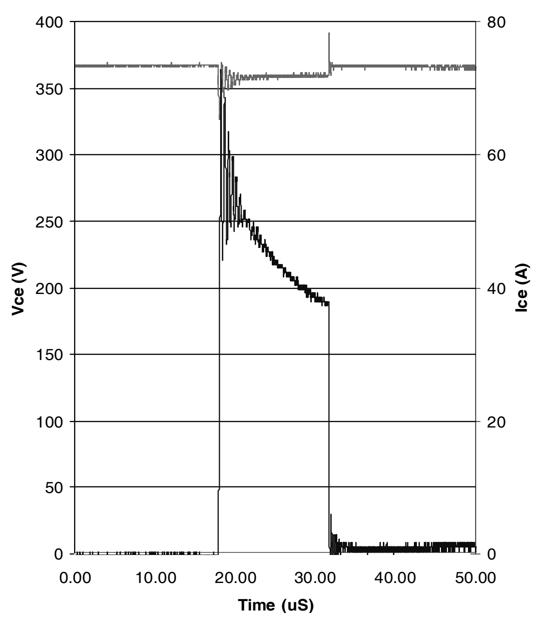
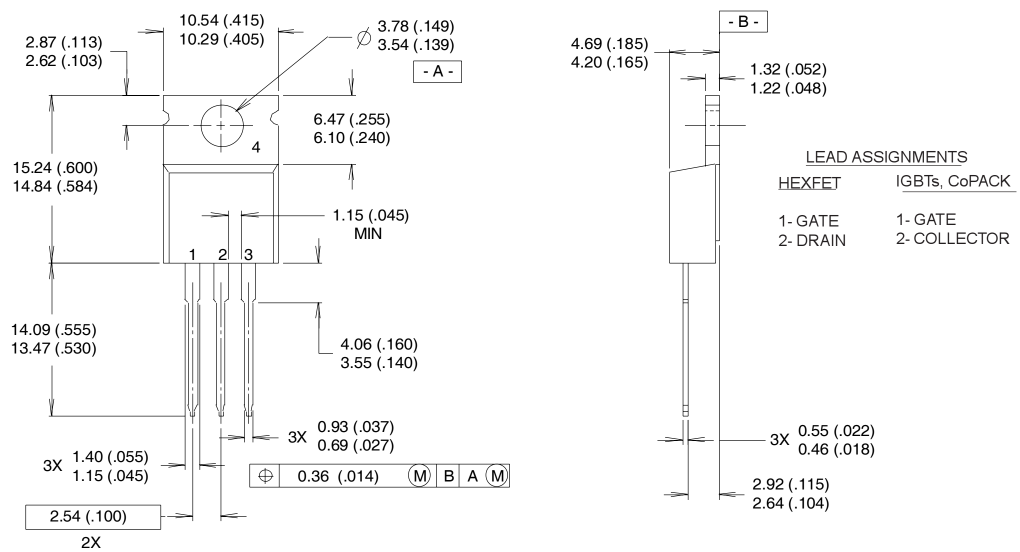


Fig. WF3- Typ. S.C Waveform
@ T_C = 150°C using Fig. CT.3

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.

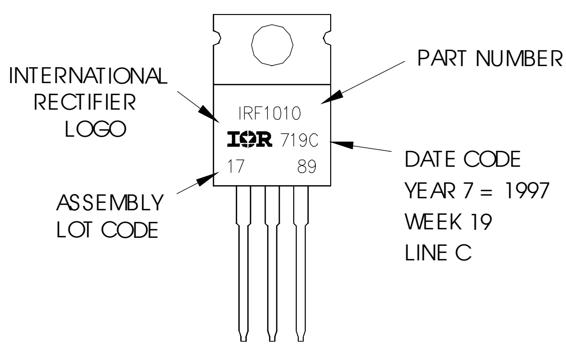
2 CONTROLLING DIMENSION : INCH

3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.

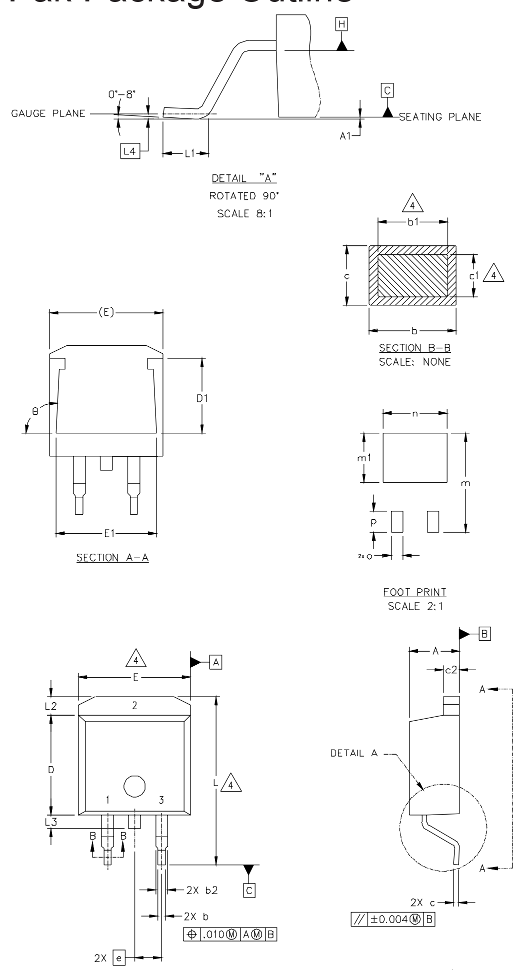
4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"



D2Pak Package Outline

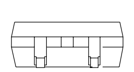


SYMBOL	DIMENSIONS MILLIMETERS MIN.	MILLIMETERS MAX.	INCHES MIN.	INCHES MAX.	NOTES
A	4.06	4.83	.160	.190	
A1		0.127		.005	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.40	.045	.055	
c	0.43	0.63	.017	.025	
c1	0.38	0.74	.015	.029	4
c2	1.14	1.40	.045	.055	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	14.61	15.88	.575	.625	
L1	1.78	2.79	.070	.110	
L2		1.65		.065	
L3	1.27	1.78	.050	.070	
L4	0.25 BSC		.010 BSC		
m	17.78		.700		
m1	8.89		.350		
n	11.43		.450		
o	2.08		.082		
p	3.81		.150		
θ	90°	93°	90°	93°	

LEAD ASSIGNMENTS

HEXFET	IGBTs, CoPACK	DIODES
1.- GATE	1.- GATE	1.- ANODE *
2.- DRAIN	2.- COLLECTOR	2.- CATHODE
3.- SOURCE	3.- EMITTER	3.- ANODE

* PART DEPENDENT.

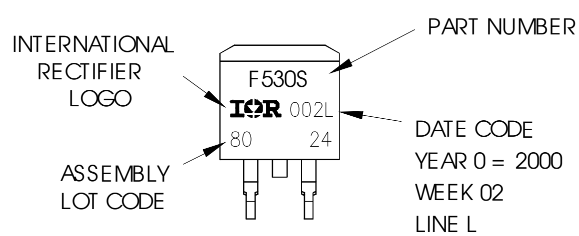


NOTES:

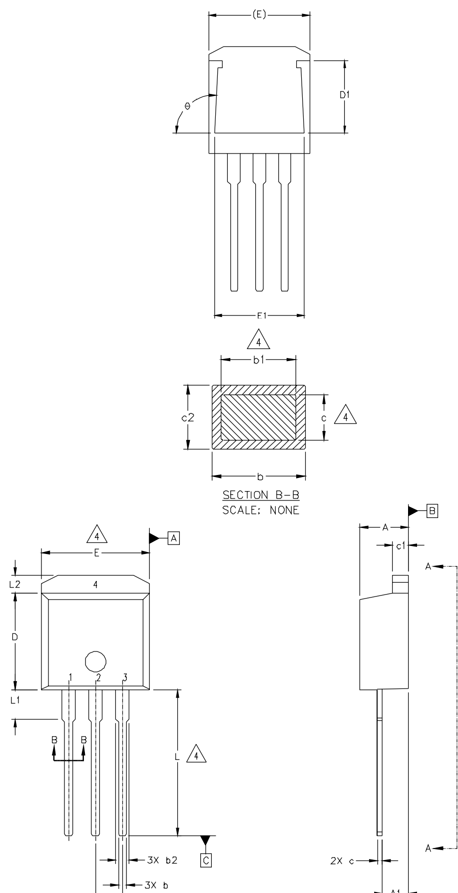
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

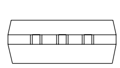
D2Pak Part Marking Information

EXAMPLE: THIS IS AN IRF530S WITH LOT CODE 8024
ASSEMBLED ON WW 02, 2000
IN THE ASSEMBLY LINE "L"



TO-262 Package Outline





SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	4.06	4.83	.160	.190	
A1	2.03	2.92	.080	.115	
b	0.51	0.99	.020	.039	
b1	0.51	0.89	.020	.035	4
b2	1.14	1.40	.045	.055	
c	0.38	0.63	.015	.025	4
c1	1.14	1.40	.045	.055	
c2	0.43	.063	.017	.029	
D	8.51	9.65	.335	.380	3
D1	5.33		.210		
E	9.65	10.67	.380	.420	3
E1	6.22		.245		
e	2.54 BSC		.100 BSC		
L	13.46	14.09	.530	.555	
L1	3.56	3.71	.140	.146	
L2		1.65		.065	

LEAD ASSIGNMENTS

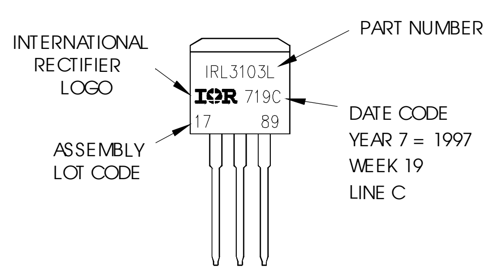
HEXFET	IGBT
1.– GATE	1- GATE
2.– DRAIN	2- COLLECTOR
3.– SOURCE	3- EMITTER
4.– DRAIN	

NOTES:

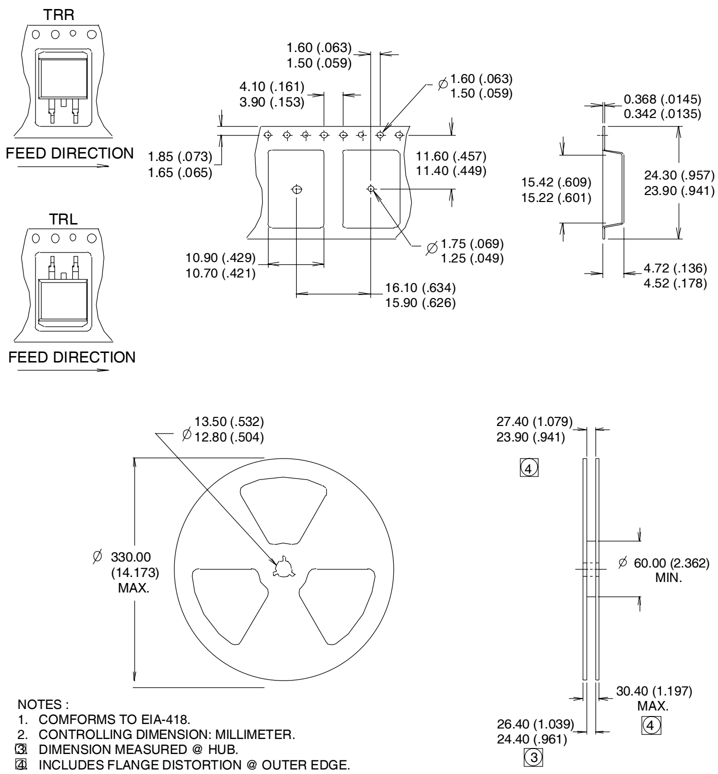
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M–1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
3. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.127 [.005"] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
4. DIMENSION b1 AND c1 APPLY TO BASE METAL ONLY.
5. CONTROLLING DIMENSION: INCH.

TO-262 Part Marking Information

EXAMPLE: THIS IS AN IRL3103L
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"



D^2Pak Tape & Reel Information



Notes:

① V_{CC} = 80% (V_{CES}), V_{GE} = 15V, L = 100µH, R_G = 50Ω.
② This is only applied to TO-220AB package.
③ This is applied to D^2Pak, when mounted on 1" square PCB (FR-4 or G-10 Material).
For recommended footprint and soldering techniques refer to application note #AN-994.
④ Energy losses include "tail" and diode reverse recovery, using Diode HF03D060ACE.

TO-220AB package is not recommended for Surface Mount Application.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

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IGR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903
Visit us at www.irf.com for sales contact information. 10/03